Doped Semiconductors Valence 3 5 Charged impurities B AL $S_i \rightarrow P adds 1e^-$ "donor" P S: -> B subtracts le "acceptor" (adds 1 ht) Ga Ge As filled valence bands Mobile charge binds to ion: empty conduction bands Ec Dopant levels can be gap~1.06 eV empty, or spin t or L E, gap ~0.01ev double occupation IJ unfavorable

What is μ ? Donor doping => $E_d < \mu < E_c$ As $T \rightarrow o$ all donated electrons enter donor states no conduction! For $T > (E_c - E_d) / k_B = 460 \text{ K}^{*}$ most are excited into C.B. A Actually a much lower T is ok due to high entropy in C.B. Read Swendson Ch. 29.10 "Semiconductor Statistics" to beam why!